

1N6626US thru 1N6631US

VOIDLESS-HERMETICALLY-SEALED SURFACE MOUNT ULTRA FAST RECOVERY GLASS RECTIFIERS

DESCRIPTION

This "Ultrafast Recovery" rectifier diode series is military qualified to MIL-PRF-19500/590 and is ideal for high-reliability applications where a failure cannot be tolerated. These industry-recognized 2.0 to 4.0 Amp rated rectifiers for working peak reverse voltages from 200 to 1000 volts are hermetically sealed with voidlessglass construction using an internal "Category I" metallurgical bond. These devices are also available in axial-leaded packages for thru-hole mounting (see separate data sheet for 1N6626 thru 1N6631). Microsemi also offers numerous other rectifier products to meet higher and lower current ratings with various recovery time speed requirements including standard, fast and ultrafast device types in both through-hole and surface mount packages. APPEARANCE

www.*Microsemi*.com

IMPORTANT: For the most current data, consult *MICROSEMI's* website: <u>http://www.microsemi.com</u>

FEATURES	APPLICATIONS / BENEFITS		
 Surface mount series equivalent to the JEDEC registered 1N6626 to 1N6631 series Voidless hermetically sealed glass package Extremely robust construction Triple-layer passivation Internal "<i>Category I</i>" Metallurgical bonds JAN, JANTX, and JANTXV available per MIL-PRF-19500/590 Further options for screening in accordance with MIL-PRF-19500 for JANS by using a "SP" prefix, e.g. SP6626US, SP6629US, etc. Axial-leaded equivalents also available (see separate data sheet for 1N6626 thru 1N6631) 	 Ultrafast recovery rectifier series 200 to 1000 V Military and other high-reliability applications Switching power supplies or other applications requiring extremely fast switching & low forward loss High forward surge current capability Low thermal resistance Controlled avalanche with peak reverse power capability Inherently radiation hard as described in Microsemi MicroNote 050 		
MAXIMUM RATINGS• Junction Temperature: $-65^{\circ}C$ to $+150^{\circ}C$ • Storage Temperature: $-65^{\circ}C$ to $+175^{\circ}C$ • Peak Forward Surge Current @ $25^{\circ}C$: $75A$ (except 1N6631 which is 60A) Note: Test pulse = 8.3ms, half-sine wave.• Average Rectified Forward Current (I ₀) at T _{EC} = $+110^{\circ}C$: $1N6626US$ thru 1N6628US 2.3 A $1N6629US$ thru 1N6631US 1.8 A (Derate linearly at $2.5\%'^{\circ}C$ for T _{EC} > $+110^{\circ}C$)• Average Rectified Forward Current (I ₀) at T _A = $25^{\circ}C$: $1N6626US$ thru 1N6631US 1.8 A (Derate linearly at $2.5\%'^{\circ}C$ for T _A > $+25^{\circ}C$: $1N6629US$ thru 1N6628US 1.75 A $1N6629US$ thru 1N6631US 1.40 A (Derate linearly at $0.80\%'^{\circ}C$ for T _A > $+25^{\circ}C$. This I ₀ rating is for PC boards where thermal resistance from mounting point to ambient is sufficiently controlled where T _{J(max)} is not exceeded. See latest issue of MIL-PRF-19500/590)• Thermal Resistance junction to endcap (R _{0JEC}): $6.5^{\circ}C/W$ • Capacitance at V _R = 10 V: 40 pF	 MECHANICAL AND PACKAGING CASE: Hermetically sealed voidless hard glas with Tungsten slugs TERMINATIONS: End caps are Copper with Tin/Lead (Sn/Pb) finish. Note: Previous inventory had solid Silver end caps with Tin/Lead finish. MARKING: Cathode band only POLARITY: Cathode indicated by band Tape & Reel option: Standard per EIA-481-B Weight: 539 mg See package dimensions and recommended pad layout on last page 		

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50 μΑ				T₄=25°C					
				1 _A -20 0	T _A =150°C	t _{rr} Note 1	t _{rr} Note 2	100 A/μs Note 2	t _r = 12 ns
/	V @ A	V @ A	V	μA	μA	ns	ns	Α	V
20	1.35V @ 2.0 A	1.50V @ 4.0 A	200	2.0	500	30	45	3.5	8
10	1.35V @ 2.0 A	1.50V @ 4.0 A	400	2.0	500	30	45	3.5	8
60	1.35V @ 2.0 A	1.50V @ 4.0 A	600	2.0	500	30	45	3.5	8
30	1.40V @ 1.4 A	1.70V @ 3.0 A	800	2.0	500	50	60	4.2	12
90	1.40V @ 1.4 A	1.70V @ 3.0 A	900	2.0	500	50	60	4.2	12
00	1.60V @ 1.4 A	1.95V @ 2.0 A	1000	4.0	600	60	80	5.0	20
30 90		1.40V @ 1.4 A 1.40V @ 1.4 A 1.60V @ 1.4 A	1.40V @ 1.4 A 1.70V @ 3.0 A 1.40V @ 1.4 A 1.70V @ 3.0 A 1.60V @ 1.4 A 1.95V @ 2.0 A	1.40V @ 1.4 A 1.70V @ 3.0 A 800 1.40V @ 1.4 A 1.70V @ 3.0 A 900 1.60V @ 1.4 A 1.95V @ 2.0 A 1000	1.40V @ 1.4 A 1.70V @ 3.0 A 800 2.0 1.40V @ 1.4 A 1.70V @ 3.0 A 900 2.0 1.60V @ 1.4 A 1.95V @ 2.0 A 1000 4.0	1.40V @ 1.4 A 1.70V @ 3.0 A 800 2.0 500 1.40V @ 1.4 A 1.70V @ 3.0 A 900 2.0 500 1.60V @ 1.4 A 1.70V @ 2.0 A 1000 4.0 600	1.40V @ 1.4 A 1.70V @ 3.0 A 800 2.0 500 50 1.40V @ 1.4 A 1.70V @ 3.0 A 900 2.0 500 50 1.60V @ 1.4 A 1.70V @ 2.0 A 1000 4.0 600 60	1.40V @ 1.4 A 1.70V @ 3.0 A 800 2.0 500 50 60 1.40V @ 1.4 A 1.70V @ 3.0 A 900 2.0 500 50 60 1.40V @ 1.4 A 1.70V @ 3.0 A 900 2.0 500 50 60 1.60V @ 1.4 A 1.95V @ 2.0 A 1000 4.0 600 60 80	1.40V @ 1.4 A 1.70V @ 3.0 A 800 2.0 500 50 60 4.2 1.40V @ 1.4 A 1.70V @ 3.0 A 900 2.0 500 50 60 4.2 1.40V @ 1.4 A 1.70V @ 3.0 A 900 2.0 500 50 60 4.2 1.60V @ 1.4 A 1.95V @ 2.0 A 1000 4.0 600 60 80 5.0

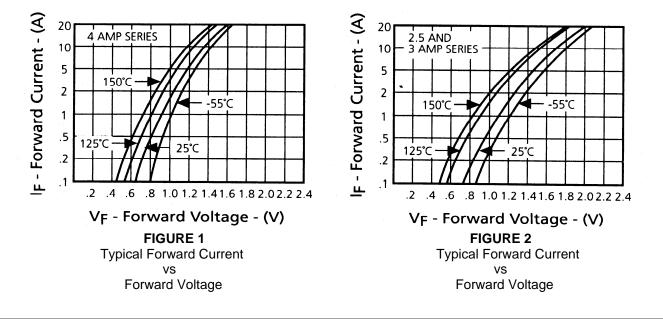
NOTE 1: Low Current Reverse Recovery Time Test Conditions: I_F=0.5A, I_{RM}=1.0A, I_{R(REC)} = 0.25A per MIL-STD-750 Method 4031, Condition B.

NOTE 2: High Current Reverse Recovery Time Test Conditions: $I_F = 2 A$, 100 A/µs MIL-STD-750, Method 4031, Condition D.

	SYMBOLS & DEFINITIONS		
Symbol	Definition		
V _{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.		
V _{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range.		
VF	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.		
I _R	Maximum Reverse Current: The maximum reverse (leakage) current that will flow at the specified voltage and temperature.		
С	Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage.		
t _{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified recovery decay point after a peak reverse current is reached.		



CHARTS AND GRAPHS



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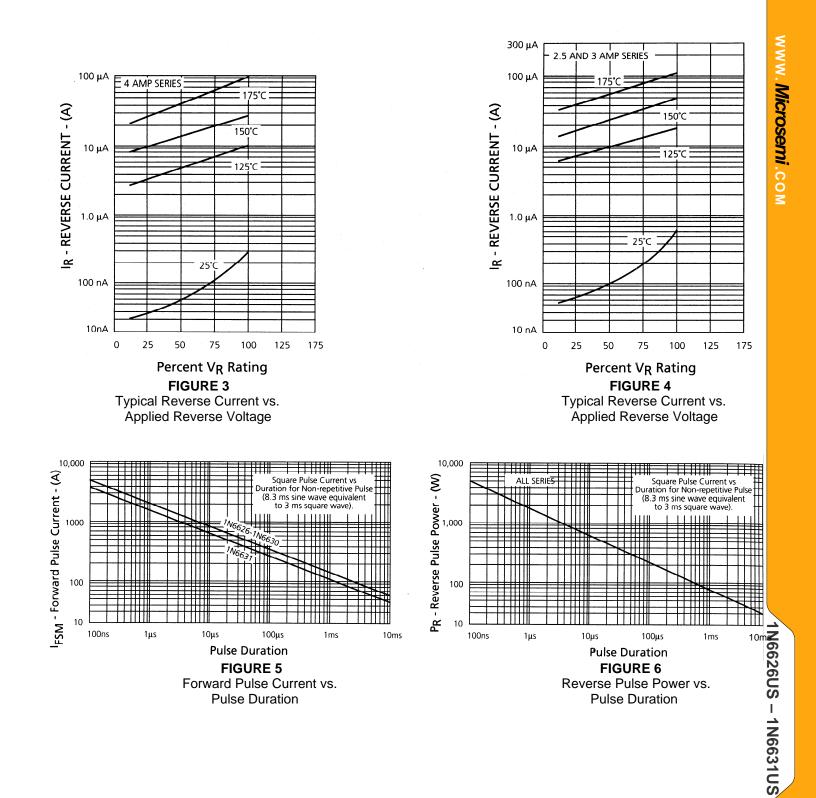
SD53A **Microsemi** Scottsdale Division 8700 E. Thomas Rd. PO Box 1390, Scottsdale, AZ 85252 USA, (480) 941-6300, Fax: (480) 947-1503

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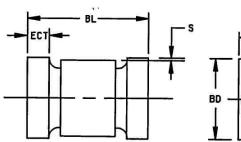
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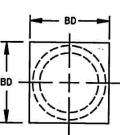
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VOIDLESS-HERMETICALLY-SEALED SURFACE MOUNT ULTRA FAST **RECOVERY GLASS RECTIFIERS**

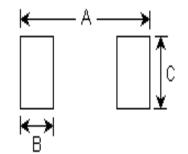
PACKAGE DIMENSIONS AND PAD LAYOUT





NOTE: This Package Outline has also previously been identified as "D-5B"

	INCHES		mm		
	MIN	MAX	MIN	MAX	
BL	.200	.225	5.08	5.72	
BD	.137	.148	3.48	3.76	
ECT	.019	.028	0.48	0.711	
S	.003		0.08		



PAD LAYOUT

INCHES mm					
Α	A 0.288 7.32				
В	0.070	1.78			
С	0.155	3.94			
Note: If mounting requires adhesive separate from the solder, an additional 0.080 inch diameter contact may be placed in the center between the pads as an optional spot for cement.					

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